

# 6-Pin DIP Optoisolators Transistor Output

The M4N26 device consists of a gallium arsenide infrared emitting diode optically coupled to a monolithic silicon phototransistor detector.

- · Most Economical Optoisolator Choice for Medium Speed, Switching Applications
- Meets or Exceeds All JEDEC Registered Specifications

### **Applications**

- · General Purpose Switching Circuits
- Interfacing and coupling systems of different potentials and impedances
- I/O Interfacing
- · Solid State Relays

### **MAXIMUM RATINGS** (T<sub>A</sub> = 25°C unless otherwise noted)

( // /			
Rating	Symbol	Value	Unit
INPUT LED			
Reverse Voltage	VR	3	Volts
Forward Current — Continuous	lF	60	mA
LED Power Dissipation @ T <sub>A</sub> = 25°C with Negligible Power in Output Detector Derate above 25°C	PD	100 1.41	mW mW/°C
Dolate above 25 C			

### **OUTPUT TRANSISTOR**

Collector–Emitter Voltage	VCEO	30	Volts
Emitter–Collector Voltage	VECO	7	Volts
Collector–Base Voltage	V <sub>СВО</sub>	70	Volts
Collector Current — Continuous	IC	50	mA
Detector Power Dissipation @ T <sub>A</sub> = 25°C with Negligible Power in Input LED	PD	150	mW
Derate above 25°C		1.76	mW/°C

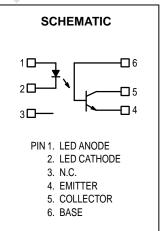
### **TOTAL DEVICE**

Isolation Surge Voltage <sup>(1)</sup> (Peak ac Voltage, 60 Hz, 1 sec Duration)	VISO	7500	Vac(pk)
Total Device Power Dissipation @ T <sub>A</sub> = 25°C Derate above 25°C	PD	250 2.94	mW mW/°C
Ambient Operating Temperature Range(2)	TA	-55 to +100	°C
Storage Temperature Range(2)	T <sub>stg</sub>	-55 to +150	°C
Soldering Temperature (10 sec, 1/16" from case)	TL	260	°C

- 1. Isolation surge voltage is an internal device dielectric breakdown rating. For this test, Pins 1 and 2 are common, and Pins 4, 5 and 6 are common.
- 2. Refer to Quality and Reliability Section in Opto Data Book for information on test conditions.

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## **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted)(1)

Characteristic	Symbol	Min	<b>Typ</b> (1)	Max	Unit
INPUT LED					
Forward Voltage (IF = 10 mA) $ T_A = 25^{\circ}\text{C} $ $ T_A = -55^{\circ}\text{C} $ $ T_A = 100^{\circ}\text{C} $	VF	_ _ _	1.15 1.3 1.05	1.5 — —	Volts
Reverse Leakage Current (V <sub>R</sub> = 3 V)	IR	_	_	100	μΑ
Capacitance (V = 0 V, f = 1 MHz)	СЈ	_	18	_	pF
OUTPUT TRANSISTOR		_			
Collector–Emitter Dark Current (V <sub>CE</sub> = 10 V, T <sub>A</sub> = 25°C)	ICEO	_	1	50	nA
$(V_{CE} = 10 \text{ V}, T_A = 100^{\circ}\text{C})$	ICEO	_	1	_	μΑ
Collector–Base Dark Current (V <sub>CB</sub> = 10 V)	ІСВО	_	0.2	_	nA
Collector–Emitter Breakdown Voltage (I <sub>C</sub> = 1 mA)	V(BR)CEO	30	45	_	Volts
Collector–Base Breakdown Voltage (I <sub>C</sub> = 100 μA)	V(BR)CBO	70	100		Volts
Emitter–Collector Breakdown Voltage (I <sub>E</sub> = 100 μA)	V(BR)ECO	7	7.8		Volts
Collector–Emitter Capacitance (f = 1 MHz, V <sub>CE</sub> = 0)	C <sub>CE</sub>	_	7		pF
Collector–Base Capacitance (f = 1 MHz, V <sub>CB</sub> = 0)	C <sub>CB</sub>	_	19	_	pF
Emitter–Base Capacitance (f = 1 MHz, V <sub>EB</sub> = 0)	C <sub>EB</sub>	_	9	_	pF
COUPLED					
Output Collector Current (I <sub>F</sub> = 10 mA, V <sub>CE</sub> = 10 V)	I <sub>C</sub> (CTR) <sup>(2)</sup>	2 (20)	7 (70)	_	mA (%)
Collector–Emitter Saturation Voltage (I <sub>C</sub> = 2 mA, I <sub>F</sub> = 50 mA)	VCE(sat)	_	0.15	0.5	Volts
Turn–On Time (I <sub>F</sub> = 10 mA, $V_{CC}$ = 10 V, $R_L$ = 100 $\Omega$ ) <sup>(3)</sup>	t <sub>on</sub>	_	2.8	_	μs
Turn–Off Time (I <sub>F</sub> = 10 mA, $V_{CC}$ = 10 V, $R_L$ = 100 $\Omega$ ) <sup>(3)</sup>	t <sub>off</sub>	_	4.5	_	μs
Rise Time (I <sub>F</sub> = 10 mA, $V_{CC}$ = 10 V, $R_L$ = 100 $\Omega$ )(3)	t <sub>r</sub>	_	2	_	μs
Fall Time (I <sub>F</sub> = 10 mA, $V_{CC}$ = 10 V, $R_L$ = 100 $\Omega$ )(3)	tf	_	2	_	μs
Isolation Voltage (f = 60 Hz, t = 1 sec)(4)	VISO	7500	_	_	Vac(pk)
Isolation Resistance (V = 500 V)(4)	R <sub>ISO</sub>	10 <sup>11</sup>	_	_	Ω
Isolation Capacitance (V = 0 V, f = 1 MHz)(4)	C <sub>ISO</sub>	_	0.2	_	pF

<sup>1.</sup> Always design to the specified minimum/maximum electrical limits (where applicable).

<sup>2.</sup> Current Transfer Ratio (CTR) = I<sub>C</sub>/I<sub>F</sub> x 100%.

<sup>3.</sup> For test circuit setup and waveforms, refer to Figure 14.

<sup>4.</sup> For this test, Pins 1 and 2 are common, and Pins 4, 5 and 6 are common.

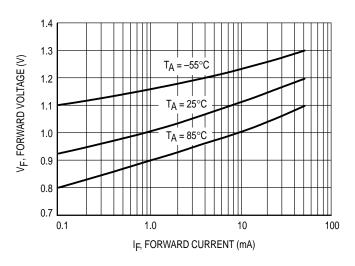


Figure 1. Forward Voltage vs. Forward Current

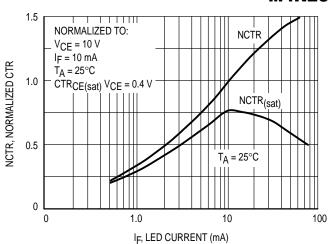


Figure 2. Normalized Non-Saturated and Saturated CTR, TA = 25°C vs. LED Current

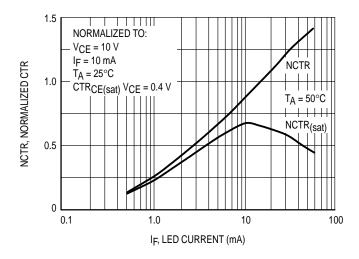


Figure 3. Normalized Non–Saturated and Saturated CTR,  $T_A = 50^{\circ}C$  vs. LED Current

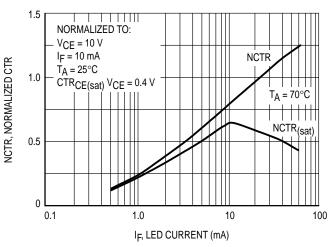


Figure 4. Normalized Non–Saturated and Saturated CTR, T<sub>A</sub> = 70°C vs. LED Current

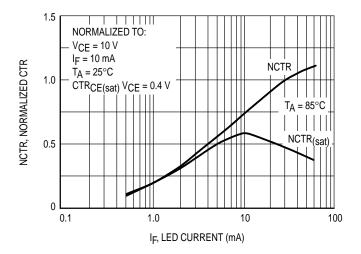


Figure 5. Normalized Non–Saturated and Saturated CTR,  $T_A = 85^{\circ}C$  vs. LED Current

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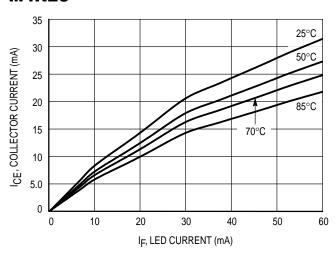


Figure 6. Collector–Emitter Current vs. Temperature and LED Current

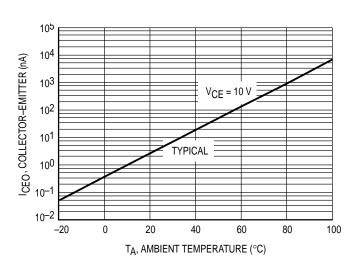


Figure 7. Collector–Emitter Leakage Current vs. Temperature

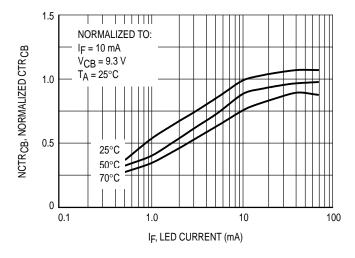


Figure 8. Normalized CTRcb vs. LED Current and Temperature

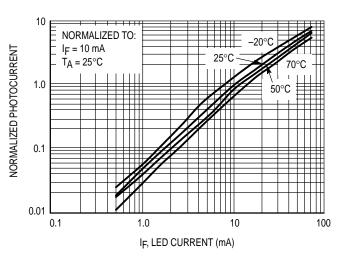


Figure 9. Normalized Photocurrent vs. IF and Temperature

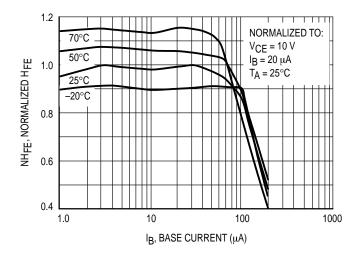


Figure 10. Normalized Non–Saturated H<sub>FE</sub> vs. Base Current and Temperature

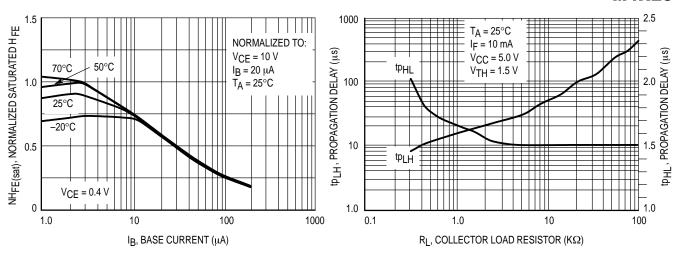


Figure 11. Normalized HFE vs. Base Current and Temperature

Figure 12. Propagation Delay vs. Collector Load Resistor

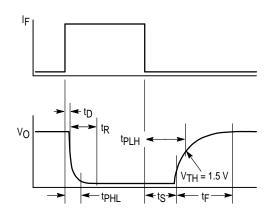


Figure 13. Switching Timing

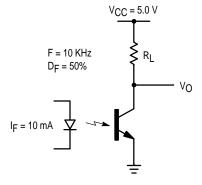
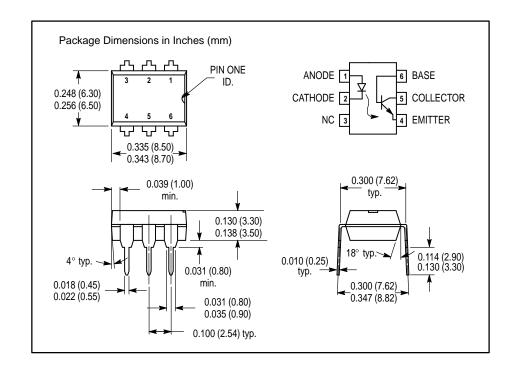


Figure 14. Switching Schematic

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